

FIELD OF THE INVENTION AND RELATED ART

15 Semiconductor integrated circuits are
miniaturized year after year, and, in order to meet
this, exposure apparatuses for transferring a circuit
pattern onto a wafer are required to have a
performance capable of transferring a finer pattern.
20 Thus, the wavelength of exposure light used in such
exposure apparatuses becomes shorter and shorter.
Currently, i-line (wavelength 365 nm) or KrF excimer
laser light (wavelength 245 nm) are used widely.
Further, use of ArF excimer laser light (wavelength
25 193 nm) has been started, and use of F₂ laser light
has been attempted.

Generally, such exposure apparatuses have a

structure that ultraviolet light from a lamp or a laser goes through a beam shaping unit and, by means of an illumination optical system which includes secondary light sources and a lens or mirror system, the light is transformed into light having a desired shape and a luminance distribution, by which a reticle is illuminated. A circuit pattern formed on the reticle is reduced at a desired magnification, through a projection optical system, and is transferred to a wafer.

As regards optical elements in exposure apparatuses such as lenses or mirrors, for example, there frequently occurs adhesion of depositions on the surface of an optical element due to impurities contained in a surrounding ambience. It is known that typically ammonium sulfate or silicon dioxide, for example, is deposited on the surface of an optical element. The product source, inside a clean room, may be ammonia vapor produced from a concrete, sulfuric acid used for removal of a resist, sulfur oxides usually contained in an atmosphere, or silicon resin used in a wall material or floor material. Inside an exposure apparatus, on the other hand, the source may be HMDS, for example, used as a contact enhancing agent with a resist. In order to remove these impurities contained in the air inside the clean room or in the exposure apparatus, a filter or the like may

09829915 "0411001
B1

5

15

20

20

However, it is practically difficult to purge the entire path of exposure light. Particularly, in the neighbourhood of a reticle or a wafer, there is a stage which is movable. Therefore, it is difficult to separate only the light path from the surrounding ambience and to purge the same. Further, there are cases wherein the light path between adjacent units extends through a surrounding ambience. In addition, while there are optical elements provided at a light entrance port and a light exit port of each container, containing a unit of optical elements, the surfaces of these optical elements facing the surrounding ambience are exposed directly to the ambience and, therefore, depositions may be adhered to them. This leads to

degradation of the optical performance, such as a decrease of illuminance, for example, and thus it causes a necessity of periodic washing or replacement.

5 Particularly, one of optical elements of a projection optical system which is closest to a wafer is directly exposed to a gas produced from a resist. As a result, the transmission factor of it decreases most. In order to avoid this, a gas may be flown in one direction, along a space between a wafer and a lens, such as shown in Figure 2. Here, in exposure apparatuses, any fluctuation in an ambience is adversely influential to the imaging performance. Further, in scan type exposure apparatuses, since a stage moves, a gas from a resist is easily mixed. It is therefore very difficult to decrease the impurity concentration at the lens surface effectively.

10 In these methods, a gas product from a wafer is rather conveyed to the lens surface, along the gas flow, such that sufficient contamination prevention is not attainable. Japanese Laid-Open Patent Application, Laid-Open No. 26038/1994 shows a method in which an inactive gas is supplied through a supply port provided on a stage, in parallel to a wafer and, simultaneously, a gas is supplied toward the wafer from the bottom end of a projection optical system, in parallel to the optical axis. This method has paid a particular note to an oxygen concentration in the

09029915 "041101

Sub
Q3
ended

10 space from the projection optical system to the wafer,
but the efficiency itself regarding the contamination
prevention at the bottom face of the projection
optical system is not so good. Between a projection
lens and the surface of a wafer, measurement light for
measuring the imaging position passes. Any change in
temperature or pressure of an ambience in the space
through which the measurement light passes, leads to a
measurement error, and this applies a large influence
15 to the position adjustment for the wafer imaging
position. Further, a change in temperature or
pressure of the ambience is also influential to the
imaging performance. For these reasons, the flow of a
gas of large flow rate or any fluctuation in pressure
or temperature causes an error of the wafer position
adjustment and degradation of the imaging performance.

00000015.041101
TOT+0"ST662860

Sub
Q4

SUMMARY OF THE INVENTION

20 It is accordingly an object of the present
invention to provide an optical structure and/or a
method of preventing contamination of the same, in
which a clean gas is supplied efficiently to the
surface, or in the neighbourhood thereof, of an
optical element being isolated from a surrounding
25 ambience, thereby to keep the surface clean and to
prevent adhesion of depositions thereon. This assures
minimization of the influence of the gas flow to the

imaging performance and adjustment of the imaging position, for example, such that contamination of the optical element can be prevented with a very small amount of gas flow.

5 In accordance with an aspect of the present invention, there is provided an optical structure, comprising: an optical element; and gas supplying means for supplying a gas to a limited portion of a surface of the optical element, wherein said gas
10 supplying means blows the gas directly against the surface of the optical element.

In one preferred form of this aspect of the present invention, light to be incident on said optical structure may be ultraviolet light.

15 The light may have one of wavelengths of 365 nm, 245 nm, 193 nm and 157 nm.

The optical structure may further comprise a plurality of optical elements and a container isolated from a surrounding ambience, wherein said plurality of
20 optical elements may be disposed at least at a light entrance surface and a light exit surface of said container, and wherein said gas supplying means may be provided at the light entrance surface and/or the light exit surface of said container.

25 There may be a plurality of gas supplying means, each being said gas supplying means, which may be disposed revolutionally symmetrically with respect

09020915 041101

to an optical axis of the optical element.

5 The optical structure may further comprise a cover for suppressing diffusion of the gas supplied by said gas supplying means to the limited portion of the surface of the optical element.

The gas supplying means may include means for removing an impurity contained in the gas to be supplied to the limited portion of the surface of the optical element.

10 The optical structure may further comprise a gas supplying equipment having impurity removing means, for supplying a gas to said gas supplying means.

15 The gas supplied by said gas supplying means may be an inactive gas.

The gas supplied by said gas supplying means may be an atmosphere, wherein, after an impurity contained is removed by impurity removing means, the gas may be supplied by said gas supplying means.

20 The optical structure may further comprise means for adjusting a gas supplying flow rate and a pressure of the gas to be supplied by said gas supplying means, in accordance with the state of use of said optical structure.

25 The optical structure may further comprise means for adjusting a temperature of the gas to be supplied by said gas supplying means.

09005915 "041101

The optical structure may further comprise gas exhausting means for exhausting the gas supplied by said gas supplying means.

5 There may be a plurality of gas exhausting means disposed revolutionally symmetrically with respect to an optical axis of the optical element.

10 The gas supplying means may be disposed at one side of the optical element, and said gas exhausting means may be disposed at the other side of the optical element.

15 The optical structure may further comprise means for adjusting a gas discharging flow rate and a pressure of the gas to be exhausted by said gas exhausting means, in accordance with the state of use of said optical structure.

20 The optical structure may further comprise (i) a plurality of optical elements, (ii) a plurality of gas supplying means each being said gas supplying means and disposed revolutionally symmetrically with respect to an optical axis of the optical element, (iii) a container isolated from a surrounding ambience, wherein said plurality of optical elements may be disposed at least at a light entrance surface and a light exit surface of said container, and (iv) a
25 cover for covering the light entrance surface and/or the light exit surface of said container, wherein said plurality of gas supplying means may be provided

09829915.041101

inside said cover.

5 The optical structure may further comprise
(i) a plurality of optical elements, (ii) a plurality
of gas supplying means each being said gas supplying
means and disposed revolutionally symmetrically with
respect to an optical axis of the optical element,
(iii) a plurality of gas exhausting means each being
said gas exhausting means and disposed revolutionally
symmetrically with respect to the optical axis of the
10 optical element, (iv) a container isolated from a
surrounding ambience, wherein said plurality of
optical elements may be disposed at least at a light
entrance surface and a light exit surface of said
container, and (v) a cover for covering the light
15 entrance surface and/or the light exit surface of said
container, wherein said plurality of gas supplying
means and said plurality of gas exhausting means may
be provided inside said cover.

20 In accordance with another aspect of the
present invention, there is provided an exposure
apparatus for illuminating a pattern with light from a
light source and for projecting light from the pattern
onto a surface to be exposed, said apparatus
comprising: an optical structure as recited above,
25 wherein the light from the light source is light of
ultraviolet region.

In one preferred form of this aspect of the

09829915 1041101

Sub
95

present invention, the light may have one of wavelengths of 365 nm, 245 nm, 193 nm and 157 nm.

The gas supplying means may blow the gas against an optical element disposed opposed to the surface to be exposed.

In accordance with a further aspect of the present invention, there is provided a device manufacturing method, comprising the steps of: exposing a wafer with a pattern by use of an exposure apparatus as recited above; and developing the exposed wafer.

In accordance with a yet further aspect of the present invention, there is provided an optical structure, comprising: an optical element; and gas supplying means for supplying a gas to a surface of the optical element, wherein the gas supplied to the surface of the optical element defines a laminar flow at and adjacent the surface of the optical element.

In one preferred form of this aspect of the present invention, light to be incident on said optical structure may be ultraviolet light.

The light may have one of wavelengths of 365 nm, 245 nm, 193 nm and 157 nm.

The optical structure may further comprise a plurality of optical elements and a container isolated from a surrounding ambience, wherein said plurality of optical elements may be disposed at least at a light

0983991004104

Sub
H6

entrance surface and a light exit surface of said container, and wherein said gas supplying means may be provided at the light entrance surface and/or the light exit surface of said container.

5 There may be a plurality of gas supplying means, each being said gas supplying means, which may be disposed along a direction substantially perpendicular to a gas supplying direction of said gas supplying means.

10 The optical structure may further comprise a cover for suppressing diffusion of the gas supplied by said gas supplying means to a limited portion of the surface of the optical element.

15 The gas supplying means may include means for removing an impurity contained in the gas to be supplied to a limited portion of the surface of the optical element.

20 ~~The optical structure may further comprise a gas supplying equipment having impurity removing means, for supplying a gas to said gas supplying means.~~

 The gas supplied by said gas supplying means may be an inactive gas.

25 The gas supplied by said gas supplying means may be an atmosphere and wherein, after an impurity contained is removed by impurity removing means, the gas may be supplied by said gas supplying means.

09029915.041101

Sub
97

The optical structure may further comprise means for adjusting a gas supplying flow rate and a pressure of the gas to be supplied by said gas supplying means, in accordance with the state of use of said optical structure.

The optical structure may further comprise means for adjusting a temperature of the gas to be supplied by said gas supplying means.

The optical structure may further comprise gas exhausting means for exhausting the gas supplied by said gas supplying means.

There may be a plurality of gas exhausting means disposed along a direction perpendicular to a direction in which the gas may be discharged by said gas exhausting means.

The gas supplying means may be disposed at one side of the optical element, and said gas exhausting means may be disposed at the other side of the optical element.

The optical structure may further comprise means for adjusting a gas discharging flow rate and a pressure of the gas to be exhausted by said gas exhausting means, in accordance with the state of use of said optical structure.

The optical structure may further comprising (i) a plurality of optical elements, (ii) a plurality of gas supplying means disposed along a direction

09020915.041101

Sub
9/8

substantially perpendicular to a direction in which
the gas is to be supplied, (iii) a container isolated
from a surrounding ambience, wherein said plurality of
optical elements may be disposed at least at a light
5 entrance surface and a light exit surface of said
container, and (iv) a cover for covering the light
entrance surface and/or the light exit surface of said
container, wherein said plurality of gas supplying
means may be provided inside said cover.

10 The optical structure may further comprise
(i) a plurality of optical elements, (ii) a plurality
of gas supplying means disposed along a direction
substantially perpendicular to a direction in which
the gas is to be supplied, (iii) a plurality of gas
15 exhausting means disposed along a direction
substantially perpendicular to a direction in which
the gas is discharged, (iv) a container isolated from
a surrounding ambience, wherein said plurality of
optical elements may be disposed at least at a light
20 entrance surface and a light exit surface of said
container, and (v) a cover for covering the light
entrance surface and/or the light exit surface of said
container, wherein said plurality of gas supplying
means and said plurality of gas exhausting means may
25 be provided inside said cover.

In accordance with a still further aspect of
the present invention, there is provided an exposure

09029915 041101

5 wherein the light from the light source is light of
ultraviolet region.

10 The gas supplying means may blow the gas
against an optical element disposed opposed to the
surface to be exposed.

These and other objects, features and
20 advantages of the present invention will become more
apparent upon a consideration of the following
description of the preferred embodiments of the
present invention taken in conjunction with the
accompanying drawings.

BRIEF DESCRIPTION OF THE DRAWINGS

Figures 1A and 1B show a first embodiment of the present invention, wherein Figure 1A is a schematic and sectional view of a projection barrel and Figure 1B is a schematic view of the bottom of the barrel.

Figure 2 is a schematic and sectional view of a conventional example.

Figure 3 is a schematic and sectional view of another example according to the first embodiment of the present invention.

Figure 4 is a schematic and sectional view of a second embodiment of the present invention.

Figures 5A and 5B are schematic and sectional views of a third embodiment of the present invention.

Figure 6 is a schematic and sectional view of another example according to the third embodiment of the present invention.

DESCRIPTION OF THE PREFERRED EMBODIMENTS

In the preferred embodiments of the present invention to be described below, the arrangements described above are applied by which a gas which may contain only a very small quantity of impurities, causing depositions, can be blown against a limited portion of the surface of an optical element, facing to a surrounding ambience, or can be flown to produce a laminar flow. Thus, an ambience with a very small

09029915 041101

Sub
89

quantity of impurities can be produced adjacent the surface of the optical element, and adhesion of deposition thereto can be suppressed. As a result, contamination of the surface of the optical element, facing to the surrounding ambience, can be prevented efficiently.

Further, gas supply ports and gas discharging ports may be provided symmetrically. This enables a revolutionally symmetrical gas flow, such that the influence to the imaging performance is small and that the impurity concentration at the lens surface can be decreased effectively.

A gas supply port may be provided at one side of the lens surface while a gas discharging port may be disposed at the opposite side of the lens surface, so that a gas is flown along the lens surface. This enables that a clean ambience is locally produced at the lens surface only by use of a small flow rate of the gas.

Preferred embodiments of the present invention will now be described with reference to the accompanying drawings.

[Embodiment 1]

Figures 1A and 1B are schematic views of a first embodiment of the present invention. This is a typical example of the present invention as applied to

09029915
04101

Sub
#10

5 a bottom lens of a projection system in a semiconductor exposure apparatus. Figure 1A is a schematic and sectional view of a projection barrel and Figure 1B is a schematic view of the bottom of the barrel.

10 As shown in Figure 1A, the projection system of the semiconductor exposure apparatus comprises a plurality of lenses 2. The whole optical system is accommodated in a barrel 1 which is closed (and purged) so that an ambient gas in a chamber ambience 10 enters into the barrel. Along the light path, the top of the projection system, that is, the lens closest to a reticle, and the bottom of the projection lens, that is, the lens 3 closest to a wafer, serve to
15 intercept the ambience.

The barrel is provided with a gas supply port 4 and a gas discharging port 6 so that a clean gas without containing impurities can be supplied to the inside of the barrel.

20 However, one face of the top most lens and one face of the bottom lens are exposed to the ambience of the exposure apparatus chamber. In consideration of it, a plurality of gas supply ports 13 are provided around the bottommost lens of the projection system, about the lens optical axis, to
25 surround the lens.

Gases 15 discharged from these gas supply

09000015.04.10.1

Sub
G11

ports flow along the lens surface toward the center of the lens. Adjacent the center, the gases flow as a downward stream, and they are diffused. In order to produce an effective flow, the flow rate and the flow speed, for example, should be controlled. To this end, an optimum shape of the discharging port 15 as well as optimum flow rate and pressure of the gas are determined in accordance with the shape and size of the lens, for example.

Further, in order to prevent mixture of a surrounding ambient gas and to aid the flow of the supplied gas, a cover 16 may effectively be provided at the lens bottom surface.

As regards the gas to be used, it should be a clean gas free from contamination causal substances. Since organic substances, SO_x, NO_x, ammonia and the like are sources of contamination, an organic substance removing filter for removing these organic substances or, alternatively, a chemical filter for removing inorganic substances, may be used as required.

Exposure apparatuses may be individually equipped with impurity removing devices such as filters. However, a gas supplied from a factory or an experimental equipment, having an impurity removing function, may be used.

The type of gas to be used may be chosen in

0909915-041101

Suby
8/12

accordance with the wavelength of ultraviolet rays,
for example, to be used in the exposure apparatus. An
atmosphere may be used where i-line or KrF laser is
used. Where light of shorter wavelength is used, an
5 inactive gas such as nitrogen or He, for example, may
be used. Where an inactive gas is supplied directly
from a commercially available high purity cylinder,
for example, since substantially no impurity is
contained therein, the impurity removing device may be
10 omitted.

With the procedure described above, there
occurs substantially no adhesion of depositions on the
lens surface. Since the gas is supplied toward a
limited area on the lens surface, there arises
15 substantially no influence to the wafer position
measurement. In the case of a scan type exposure
apparatus, the influence of resist gas diffusion due
to the motion of the wafer stage, for example, can be
made small.

20 A valve 14 for adjusting the flow rate of the
supplied gas may be controlled so as to adjust the gas
flow rate in accordance with the state of exposure
operation. This enables more effective supply of a
clean gas to the lens surface. For example, during an
25 alignment process, during an imaging position
measuring process or during an exposure process, the
flow of a gas applies a large influence to the imaging

09829915-041101

Sub
8/13

performance. Therefore, the gas flow rate should be restricted. On the other hand, during a wafer conveying process, for example, the gas flow can be increased. Thus, when a new wafer is conveyed onto a wafer stage, the supplying flow rate may be increased, thereby to effectively remove an impurity gas, produced from a resist, away from the lens. During the alignment and exposure process, the flow rate may be decreased to prevent adverse influence to the imaging performance.

Where a gas of the same type as of the gas used inside the barrel can be used and flown along the lens surface, as shown in Figure 3, the gas may be supplied from a gas discharging port of the projection barrel.

[Embodiment 2]

Figure 4 is a schematic view of a second embodiment of the present invention. In the gas supplying method of the first embodiment, there may be cases wherein, depending on the size or shape of the lens, for example, the gas flown from the lens to the wafer surface is diffused by the wafer surface to cause diffusion of a resist gas. In consideration of it, as shown in Figure 4, a gas discharging port may be provided below the supply port. This is effective to produce a gas flow.

090229915.041101

July 14

Also in this case, there may be a plurality of gas discharging ports disposed revolutionally symmetrically with respect to the optical axis, like the gas supply ports.

5 Further, the shape and position of these gas supply ports and gas discharging ports should be determined so that the gas flows appropriately. Moreover, the gas supplying pressure and flow rate as well as the gas discharging pressure from the gas
10 discharging port should be adjusted appropriately. The pressure inside the projection barrel is maintained constant, and usually, the pressure difference thereof with the surrounding ambience is small. As compared therewith, from the gas
15 discharging port 17, the gas should be discharged with a pressure difference of a certain level or more, with respect to the surrounding ambience. In consideration of this, an exhausting system 33 separate from the projection barrel may be provided as required.

20

[Embodiment 3]

Figures 5A and 5B are schematic views of a third embodiment of the present invention, wherein Figure 5A is a schematic and sectional view of a
25 projection system lens barrel and Figure 5B is a schematic view of the lens bottom face.

A gas supply port 18 and a gas discharging

09829915-041101

Sub
2/15

port 20 are provided in the neighbourhood of the
bottommost lens of the projection system, that is, the
lens 3 closest to the wafer, and the lens surface of
the barrel 22 at the top of the projection system,
5 facing to the chamber ambience side, such that a clean
gas is flown. As shown in Figure 5B, the gas supply
port 18 is provided at one of lens side faces while
the gas discharging port 20 is provided at the
opposite lens side face, by which an effective gas
10 flow is produced locally upon the lens surface.
Particularly, plural gas supply ports and plural gas
discharging ports may preferably be provided. In that
occasion, a gas flows uniformly along the lens
surface.

15 Further, in accordance with the shape of the
lens (concave, convex or flat) and the curvature
thereof, an optimum gas flowing angle at the gas
supplying port may be selected to assure that the gas
flows along the lens surface. Moreover, a cover 16
20 may be provided at the chamber ambience side of the
lens, by which the influence or a surrounding gas flow
or mixture thereof can be prevented.

A flow rate adjusting valve 19 may be used to
adjust the flow rate and flow speed of the gas so that
25 a laminar flow is produced. In this method, although
the gas flow is only in one direction, the ambience at
the lens surface can be effectively kept clean with

09029915-041401

July
8/16
25

use of only a limited flow rate of the gas.
Therefore, the influence to the imaging performance or
imaging position measurement is small. Further, there
is an advantage that only a relatively narrow space is
5 required. Moreover, since a gas is flown only locally
on the lens surface, in the case of a scan type
exposure apparatus, the influence of resist gas
diffusion due to the motion of the stage, for example,
can be made small.

10 Between a projection optical system and a
wafer, a probe light for focus position measurement
passes. If there occurs non-uniformness of pressure
or temperature in the ambience through which the
probe light passes, it causes a measurement error.
15 In consideration of this, usually, a gas of the same
type as of the chamber ambience is used. In this
embodiment, however, since the gas flow is stable, a
gas having a refractive index different from that of
the ambience gas may be used. For example, in a case
20 where the chamber ambience is atmosphere, a nitrogen
gas may be flown. Where the barrel inside space is
purged by the same type of gas, the same gas line may
be used. If a different type of gas is to be flown, a
separate line is necessary. Where the same gas line
25 as of the chamber ambience is used, since the gas must
be sufficiently clean, gas purifying means such as a
filter may be used, as required.

05026915.041101

Sub
116
Credid

5

10

15

This embodiment is applicable not only to a projection system but also to a portion of a separate optical system such as an illumination system, for example, as shown in Figure 6. Figure 6 is a schematic and sectional view of an optical system, wherein an optical system 23 is accommodated inside a barrel 22 being isolated from a surrounding ambience. Along the optical path, the ambience is isolated by means of a seal glass 24 which comprises a parallel flat plate. The inside of the barrel is purged by a clean gas, through a gas supply port 25 and a gas discharging port 26. In order that a clean gas flows along the surface of the seal glass 24, being in contact with the surrounding ambience, a gas supplying port 27 is provided at one side face while a gas discharging port 28 is provided at the opposite side face. By adjusting the flow rate and the pressure, a gas is flown along the seal glass surface.

20

Like the third embodiment described above, the first and second embodiments described hereinbefore are applicable also to an optical system other than a projection system. Further, they can be applied not only to an exposure apparatus but also to an optical system which uses ultraviolet rays.

25

In accordance with the embodiments of the present invention described hereinbefore, a clean gas is efficiently supplied to the surface, or adjacent

Sub
117

09029915-041101

thereto, of the surface of an optical element isolated from a surrounding ambience, which surface faces to the surrounding ambience. This assures that the surface of the optical element is kept clean, and
5 adhesion of depositions can be prevented effectively. Thus, contamination prevention which is particularly suitably applicable to a semiconductor exposure apparatus, is accomplished.

Further, in accordance with the present
10 invention, plural gas supply ports and plural gas discharging ports may be disposed revolutionally symmetrically, for example. Namely, a structure harmonized with the direction or the flow rate of a gas flow is chosen. This assures that the influence
15 to the imaging performance is small and that the impurity concentration at the lens surface is lowered effectively.

Further, in accordance with the present invention, a gas supply port may be provided at one
20 side face of the lens surface while a gas discharging port may be provided at the opposite side face thereof, to ensure that a gas flows along the lens surface. With this arrangement, a clean ambience is kept locally on the lens surface even with use of a
25 very low rate of the gas flow.

Furthermore, when the present invention is applied to a scan type exposure apparatus, the

05025915-041101

influence of the scan motion of a mask or a stage
can be reduced effectively.

While the invention has been described with
reference to the structures disclosed herein, it is
not confined to the details set forth and this
application is intended to cover such modifications or
changes as may come within the purposes of the
improvements or the scope of the following claims.

10

15

20

25

09029915 041101